

N-P-N epitaxial planar transistor intended for use in class-A, B and C operated mobile, industrial and military transmitters with a supply voltage of 13,5 V. The transistor is resistance stabilized. Every transistor is tested under severe load mismatch conditions with a supply over-voltage to 16,5 V. It has a ¼" capstan envelope with a moulded cap. All leads are isolated from the stud.

QUICK REFERENCE DATA

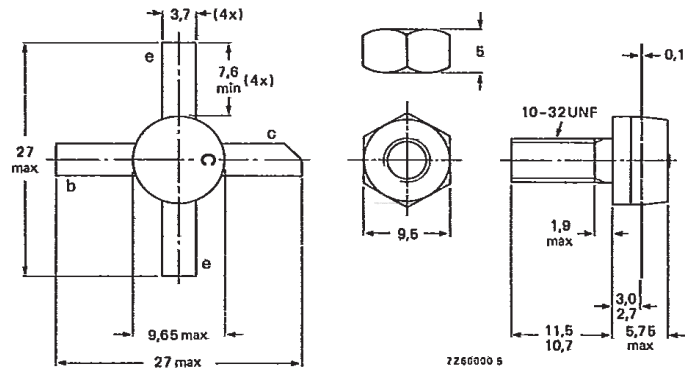
R.F. performance up to $T_{mb} = 25\text{ }^{\circ}\text{C}$ in an unneutralized common-emitter class-B circuit

mode of operation	V_{CE} V	f MHz	P_S W	P_L W	I_C A	G_p dB	η %	\bar{z}_i Ω	\bar{Y}_L mS
c.w.	13,5	175	< 6,25	25	< 2,64	> 6	> 70	$1,6 + j1,4$	$213 + j5,5$

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-56.



RATINGS Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter) peak value	V_{CBOM}	max.	36	V
Collector-emitter voltage (open base)	V_{CEO}	max.	18	V
Emitter-base voltage (open collector)	V_{EBO}	max.	4	V
Collector current (average)	$I_{C(AV)}$	max.	5	A
Collector current (peak value) $f > 1\text{ MHz}$	I_{CM}	max.	10	A
Total power dissipation up to $T_{mb} = 25\text{ }^{\circ}\text{C}$ $f > 1\text{ MHz}$	P_{tot}	max.	70	W

Note : Above parameters , ratings , limits and conditions are subject to change .